

Hi3516CV500 DDR4 Signal Integrity Report





Date	Contents	Remarks				
2019-3-16	The test is performed based on the DDR4 1866MHz standard					
Note: All the test data in this report is the test result of the HiSilicon test sample and is only for reference. Note that the tests conducted by HiSilicon cannot replace customers' related tests.						





Chipset	Hi3516CV500				
Board Name	HI3516CV500DDR4DMEB VER.A				
DRAM Part Number	MT41K256M16TW-107:P				
Oscilloscope	DSA72004C TEKTRONIX				
Temperature	25°C				
DRAM Operating Frequency	900MHz(DDR3L)				
Vdd/Vref_CA/Vref_DQ/Vcore	1.2V/0.6V/Trainning/0.9V				
DRAM_ODT	120ohm				
SOC_ODT	120ohm				
DRAM_RON	40ohm				
SOC_RON	CK=34ohm 1T(CS/CKE/ODT)=34ohm 2T=34ohm DQ=40ohm DQS=40ohm				

Signal Integrity Summary& Conclusion



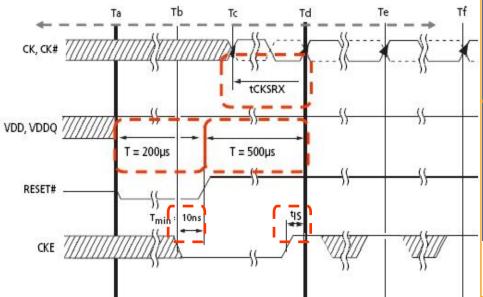
	Judgment&Summary					
Management Have	Decult	Domonto				
Measurement Item	Result	Remark				
Sequence Check	PASS					
Power Check	PASS					
Signal Integrity Check	PASS					

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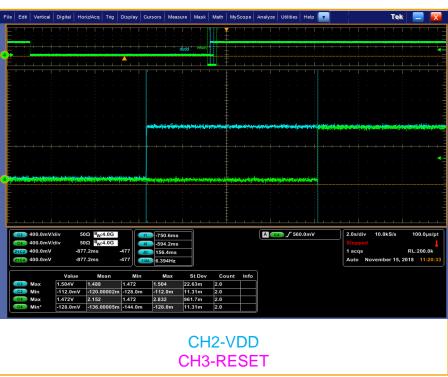
Power Up Initialization Sequence Check Result

SPEC

3.3.1 Power-up Initialization Sequence (Cont'd)



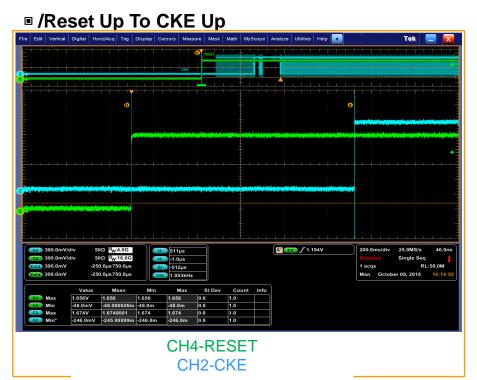
Stable VDD to /Reset Up



Parameter	Time	Spec	Result	Remark
Stable VDD to /Reset Up	156ms	Min:200us	PASS	/RESET needs to be maintained for minimum 200us with stable power. (JEDEC spec.)

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Power Up Initialization Sequence Check Result

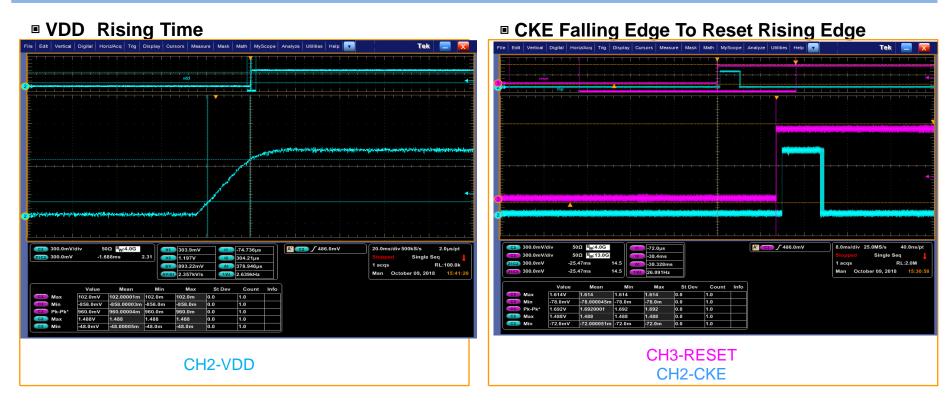




Parameter	Time	Spec	Result	Remark
/Reset Up To CKE Up	512us	Min:500us	PASS	After /RESET is de-asserted. Wait for another 500us until CKE becomes active.(JEDEC spec.)
tCKSRX	>30ns	Min: Max(5nCK,10ns)	PASS	Clocks (CK, CK#) need to be started and stabilized for at least 10 ns or 5 tCK (which is larger) before CKE goes active.(JEDEC spec.)

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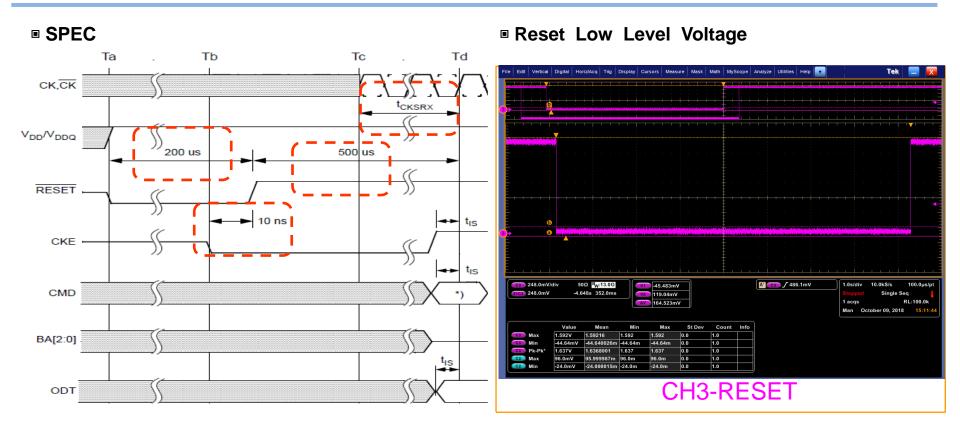
Power Up Initialization Sequence Check Result



Parameter	Time	Spec	Result	Remark
VDD Rising Time	379us	Max:200ms	PASS	The power voltage ramp time between 300 mv to VDDmin must be no greater than 200 ms.(JEDEC spec.)
CKE Falling Edge to Reset Rising Edge	>38.4ms	Min:10ns	PASS	CKE is pulled "Low" anytime before RESET# being de-asserted (min. time 10 ns).

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Reset Initialization Sequence Check Result



Parameter	Voltage	Spec	Result	Remark
Reset Low Level Voltage	164.5mV	Max: 300mV	PASS	Reset Low Level Voltage must be within 300 mV.

Average Periodic Refresh Interval Check Result



SPEC

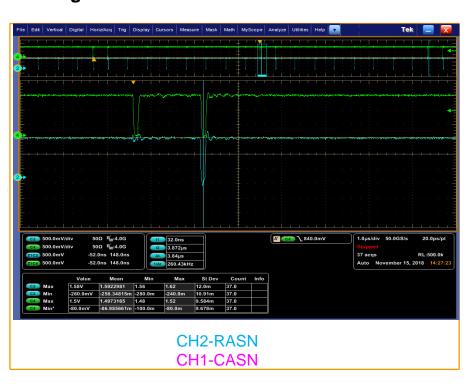
12.2 Refresh parameters by device density

Table 61 — Refresh parameters by device density

Parameter	Symbol		512Mb	1Gb	2Gb	4Gb	8Gb	Units	Notes
REF command to ACT or REF command time	tRFC		90	110	160	300	350	ns	
Average periodic refresh	tREFI	0 °C ≤ T _{CASE} ≤ 85 °C	7.8	7.8	7.8	7.8	7.8	μs	
interval		85 °C < T _{CASE} ≤ 95 °C	3.9	3.9	3.9	3.9	3.9	μs	1

NOTE 1. Users should refer to the DRAM supplier data sheet and/or the DIMM SPD to determine if DDR3 SDRAM devices support the following options or requirements referred to in this material.

Average Periodic Refresh Interval



Parameter	Time	Spec	Result	Remark
tREFI	3.84us	Max:7.8us	PASS	

Power Check Result



■ AC Peak-Peak Noise Check Result

Parameter	Spec (PK-PK)	Value (PK-PK)	Unit	Result	Position	Test Point
VDD_IO	NA	34	mV	NA	DRAM	C283
VREFCA	30	14.2	mV	PASS	DRAM	C153
VREFDQ	30	14.4	mV	PASS	DRAM	C156

VDD_IO Supply Voltage

Parameter	Spec	Value	Unit	Result	Position	Test Point
VDD_IO	Min:1.283	1.355	V	PASS	SOC	LB20
	Max:1.45	1.356	V	PASS	DDR	R174





■ Clock Signal Integrity Test Result

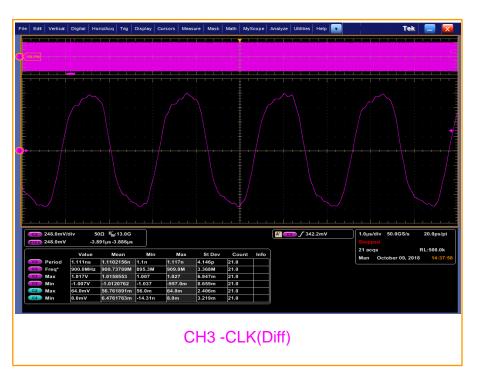
Parameter	Spec (Min)	Spec (Max)	Measurement data (Min)	Measurement data (Max)	Unit	Remark
Vix	-150	150	-114.33	93	mV	PASS
tCK(avg)	1.07	1.25	1.110	1.112	ps	PASS
tCH(avg)	470	530	506	508	mtCK(avg)	PASS
tCL(avg)	470	530	491	494	mtCK(avg)	PASS
tJIT(per)	-70	70	-17.3	20.5	ps	PASS
tJIT(cc)	-140	140	-15.5	18.8	ps	PASS
InputSlew-Diff- Rise	-	-	-	10.108	V/ns	-
InputSlew-Diff- Fall	-	-	-	-6.3436	V/ns	-

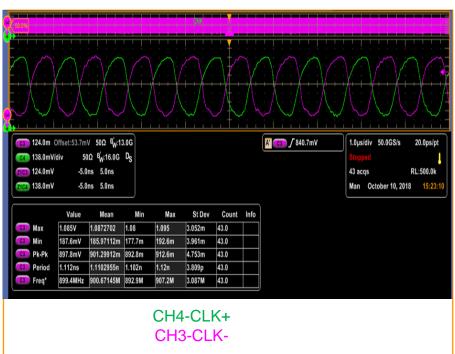
Signal Integrity Test Result (Clock)



CLK With Differential Measurement

©CLK Vix With High Voltage Trigger





Signal Integrity Test Result (CMD&ADDR)



■ SPEC

Symbol	Reference	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	DDR3-2133	Units
tIS(base) AC175	V _{IH/L(ac)}	200	125	65	45	-	-	ps
tIS(base) AC150	V _{IH/L(ac)}	350	275	190	170	-	-	ps
tIS(base) AC135	V _{IH/L(ac)}	-	-	-	-	65	60	ps
tIS(base) AC125	V _{IH/L(ac)}	-	-	-	-	150	135	ps
tIH(base) DC100	V _{IH/L(dc)}	275	200	140	120	100	95	ps

	ΔtIS, ΔtIH derating in [ps] AC/DC based Alternate AC125 Threshold -> VIH(ac)=VREF(dc)+135mV, VIL(ac)=VREF(dc)-135mV																
			CK,CK# Differential Slew Rate														
		4.0	V/ns	3.0	V/ns	2.0	V/ns	1.8	V/ns	1.6	V/ns	1.4	V/ns	1.2 V/ns		1.0 V/ns	
		ΔtIS	ΔtIH	ΔtIS	ΔtIH	ΔtIS	ΔtIH	ΔtIS	ΔtIH	ΔtIS	ΔtIH	ΔtIS	ΔtIH	ΔtIS	ΔtIH	ΔtIS	ΔtIH
	2.0	68	50	68	50	68	50	76	58	84	66	92	74	100	84	108	100
	1.5	45	34	45	34	45	34	53	42	61	50	69	58	77	68	85	84
	1.0	0	0	0	0	0	0	8	8	16	16	24	24	32	34	40	50
ADD	0.9	2	-4	2	-4	2	-4	10	4	18	12	26	20	34	30	42	46
Slew	0.8	3	-10	3	-10	3	-10	11	-2	19	6	27	14	35	24	43	40
rate V/ns	0.7	6	-16	6	-16	6	-16	14	-8	22	0	30	8	38	18	46	34
	0.6	9	-26	9	-26	9	-26	17	-18	25	-10	33	-2	41	8	49	24
	0.5	5	-40	5	-40	5	-40	13	-32	21	-24	29	-16	37	-6	45	10
	0.4	-3	-60	-3	-60	-3	-60	6	-52	14	-44	22	-36	30	-26	38	-10





Command Signal Integrity Test Result

CMD /ADD	Input Setup Time (tIS)@AC150 tIS(min)(ps)	Input Hold Time (tIH)@DC100 tIH(min) (ps)	Input Slew Rate (Rising Time) (V/ns)	Input Slew Rate (Falling Time) (V/ns)
SPEC	133	150		
CS_N	552	476	2.08	-3. 16
ODT	533	491	2. 25	-2.54

Signal Integrity Test Result (CMD&ADDR)



■ 1T_CMD_ADDR CS_N











Address Signal Integrity Test Result

CMD /ADD	Input SetupTime (tIS)@AC150 tIS(min)(ps)	Input Hold Time (tIH)@DC100 tIH(min) (ps)	Input Slew Rate (RisingTime) (V/ns)	Input Slew Rate (FallingTime) (V/ns)
SPEC	133	150		
A4	1001.5	1069.9	3.6	-2.4734
A7	1023.1	1042.7	3.6	-2.8045

Signal Integrity Test Result (CMD&ADDR)



2T_CMD_ADDR A4

■ 2T_CMD_ADDR A7





Signal Integrity Test Result (DATA)



■ SPEC

Symbol	Reference	DDR3- 800	DDR3- 1066	DDR3- 1333	DDR3- 1600	DDR3- 1866	DDR3- 2133	Units	Notes
tDS(base) AC175	V _{IH/L(ac)} SR=1V/ns	75	25	-	-	-	-	ps	2
tDS(base) AC150	V _{IH/L(ac)} SR=1V/ns	125	75	30	10	-	-	ps	2
tDS(base) AC135	V _{IH/L(ac)} SR=1V/ns	165	115	60	40			ps	2, 3
tDS(base) AC135	V _{IH/L(ac)} SR=2V/ns	-	-	-	-	<mark>6</mark> 8	53	ps	1
tDH(base) DC100	V _{IH/L(dc)} SR=1V/ns	150	100	65	45	-	-	ps	2
tDH(base)DC100	V _{IH/L(dc)} SR=2V/ns					70	55	ps	1

	∆tDS, ∆tDH derating in [ps] AC/DC based Alternate AC135 Threshold -> VIH(ac)=VREF(dc)+135mV, VIL(ac)=VREF(dc)-135mV Alternate DC 100 Threshold -> VIH(dc)=VREF(dc)+100mV, VIL(dc)=VREF(dc)-100mV																								
			DQS,DQS# Differential Slew Rate																						
		8.0	V/ns	7.0 \	V/ns	6.0 V/ns		5.0 V/ns		4.0 V/ns		3.0 \	V/ns	2.0 \	V/ns	1.8 \	V/ns	1.6	V/ns	1.4 V/ns		1.2 V/ns		1.0 V/ns	
		ΔtDS	ΔtDH	ΔtDS	ΔtDH	∆tDS	ΔtDH	∆tDS	ΔtDH	ΔtDS	ΔtDH	ΔtDS	ΔtDH	ΔtDS	ΔtDH	∆tDS	ΔtDH	∆tDS	ΔtDH	ΔtDS	ΔtDH	∆tDS	ΔtDH	ΔtDS	ΔtDH
	4.0	34	25	34	25	34	25	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
	3.5	29	21	29	21	29	21	29	21	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
	3.0	23	17	23	17	23	17	23	17	23	17	-	-	-	-	-	-	-	-	-	-	-	-	-	-
	2.5	-	-	14	10	14	10	14	10	14	10	14	10	-	-	-	-	-	-	-	-	-	-	-	-
	2.0	-	-	-	-	0	0	0	0	0	0	0	0	0	0	-	-	-	-	-	-	-	-	-	-
DQS	1.5	-	-	-	-	-	-	-23	-17	-23	-17	-23	-17	-23	-17	-15	-9	-	-	-	-	-	-	-	-
Slew	1.0	•	-	-	-	-	-	-	-	-68	-50	-68	-50	-68	-50	-60	-42	-52	-34	-	-	-	-	-	-
V/ns	0.9	-	-	-	-	-	-	-	-	-	-	-66	-54	-66	-54	-58	-46	-50	-38	-42	-30	-	-	-	-
	0.8	-	-	-	-	-	-	-	-	-	-	-	-	-64	-60	-56	-52	-48	-44	-40	-36	-32	-26	-	-
	0.7	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-53	-59	-45	-51	-37	-43	-29	-33	-21	-17
	0.6	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	•	-43	-61	-35	-53	-27	-43	-19	-27
	0.5	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-39	-66	-31	-56	-23	-40
	0.4	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-38	-76	-30	-60

Signal Integrity Test Result (DATA)



■ Data Signal Integrity Test Result

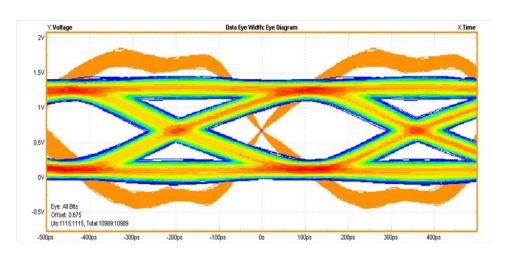
Parameter	Spec	Unit	DQ7	DQ14	Remarks
Input Slew Rate(Setup-time)	-	V/ns	5.7	3.12	-
Input Slew Rate(Hold-time)	-	V/ns	-5.7	-3.51	-
Input Setup- Time(tDS)@AC135 [tDS(base)=68ps]	min:99	ps	128.65	107.41	PASS
Input Hold-Time(tDH)@DC100 [tDH(base)=70ps]	min:95	ps	214.09	241.41	PASS

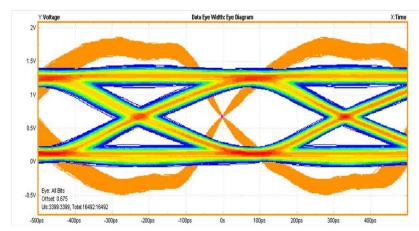




■ DQ7-Write

DQ14-Write





DDR Training write window

Max WIN: 68. DQ Index: 2 3

```
[PHY0][RANK0]:
Write window of prebit-deskew:
DQ 0 4 8 12 16 20 24 28 32 36 40 44 48 52 56 60 64 68 72 76 80 84 88 92 96 100 104 108 112 116 120 124 RANGE
Sum WIN: 1034. Avg WIN: 64
Min WIN: 61. DQ Index: 14
```

DDR Training-read window

Read window of prebit-deskew:

4 8 12 16 20 24 28 32 36 40 44 48 52 56 60 64 68 72 76 80 84 88 92 96 100 104 108 112 116 120 124 RANGE WIN 6

Sum WIN: 1019. Avg WIN: 63 Min WIN: 61. DQ Index: 12 14 Max WIN: 67. DQ Index: 2



Thank you